

## KBJ SILICON BRIDGE RECTIFIER

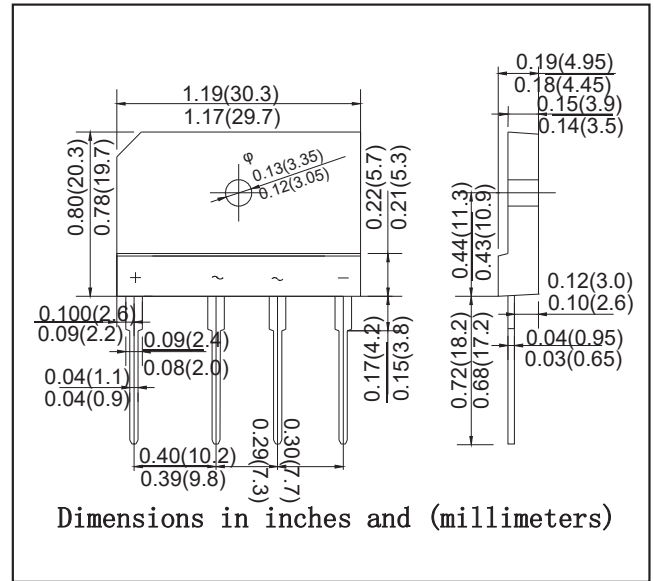
REVERSE VOLTAGE: 50 --- 1000V    CURRENT: 8.0A

### FEATURES

- Rating to 1000V PRV
- Surge overload rating to 200 Amperes peak Ideal for printed circuit board
- Reliable low cost construction utilizing molded plastic technique results in inexpensive product
- Lead solderable per MIL-STD-202 method 208

### MECHANICAL DATA

- Polarity: Symbols molded on body
- Weight: 0.23 ounces, 6.6 grams
- Mounting position: Any



### MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted) Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate by 20%.

Parameter		KBJ 8A	KBJ 8B	KBJ 8D	KBJ 8G	KBJ 8J	KBJ 8K	KBJ 8M	UNITS
Maximum recurrent peak reverse voltage	$V_{RRM}$	50	100	200	400	600	800	1000	V
Maximum RMS voltage	$V_{RMS}$	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	$V_{DC}$	50	100	200	400	600	800	1000	V
Maximum average forward Output current @ $T_A=110^\circ\text{C}$	$I_{F(AV)}$	8.0							A
Peak forward surge current 8.3ms single half-sine-wave superimposed on rated load	$I_{FSM}$	200.0							A
Maximum instantaneous forward voltage at 4.0 A	$V_F$	1.0							V
Maximum reverse current @ $T_A=25^\circ\text{C}$ at rated DC blocking voltage @ $T_A=100^\circ\text{C}$	$I_R$	10.0 1.0							$\mu\text{A}$ mA
Typical junction capacitance per element	$C_J$	55							pF
Typical thermal resistance	$R_{\theta JC}$	1.6							$^\circ\text{C}/\text{W}$
Operating junction temperature range	$T_J$	- 55 --- + 150							$^\circ\text{C}$
Storage temperature range	$T_{STG}$	- 55 --- + 150							$^\circ\text{C}$

NOTES: 1. Measured at 1.0MHz and applied reverse voltage of 4.0V DC

2. Device mounted on 300mm X 300mm X 1.6mm cu Plate heatsink.

RATINGS AND CHARACTERISTIC CURVES

FIG.1 – PEAK FORWARD SURGE CURRENT

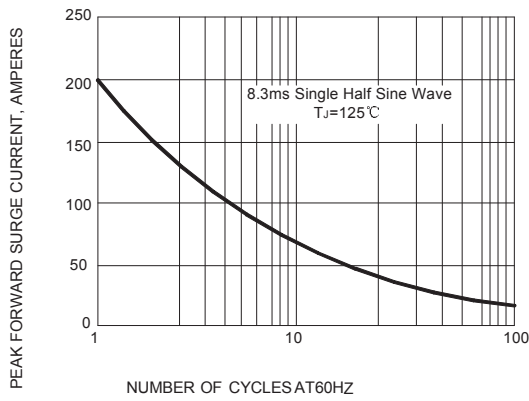


FIG.2 – FORWARD DERATING CURVE

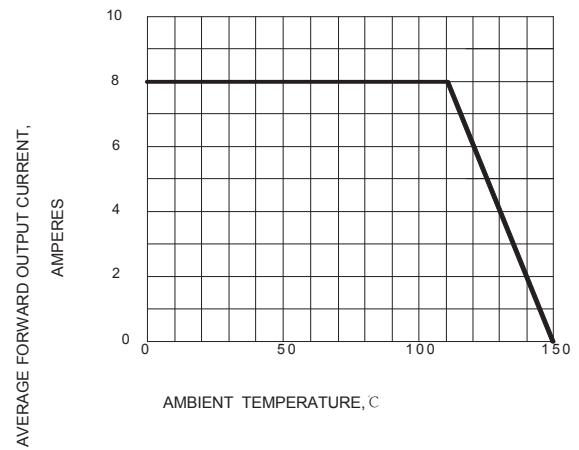


FIG.3 – TYPICAL FORWARD CHARACTERISTIC

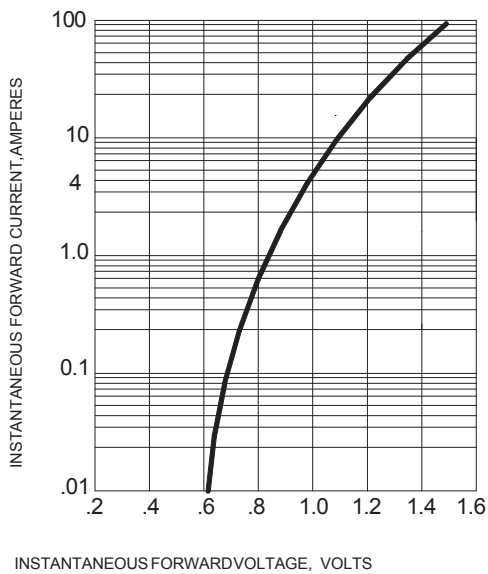


FIG.4 – TYPICAL JUNCTION CAPACITANCE

